

# BUK653R7-30C

N-channel TrenchMOS intermediate level FET

Rev. 3 — 13 October 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	30	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	<a href="#">11</a>	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	158	W
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 11</a>	-	3.3	3.9	mΩ



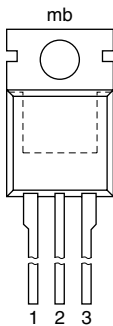
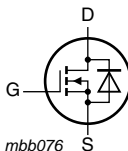
**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; unclamped	-	-	242	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 24\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	20	-	nC

[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78A (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK653R7-30C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

## 4. Limiting values

**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	30	V	
$V_{GS}$	gate-source voltage	DC	[1]	-16	16	V
		Pulsed	[2]	-20	20	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	[3]	-	100	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V};$ see <a href="#">Figure 1</a>	[3]	-	100	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}; t_p \leq 10\text{ }\mu\text{s};$ pulsed; see <a href="#">Figure 3</a>	-	583	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	158	W	
$T_{stg}$	storage temperature		-55	175	°C	
$T_j$	junction temperature		-55	175	°C	
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	[3]	-	100	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s};$ pulsed; $T_{mb} = 25\text{ °C}$	-	583	A	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped	-	242	mJ	
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		[4][5][6]	-	J	

[1] -16V accumulated duration not to exceed 168 hrs

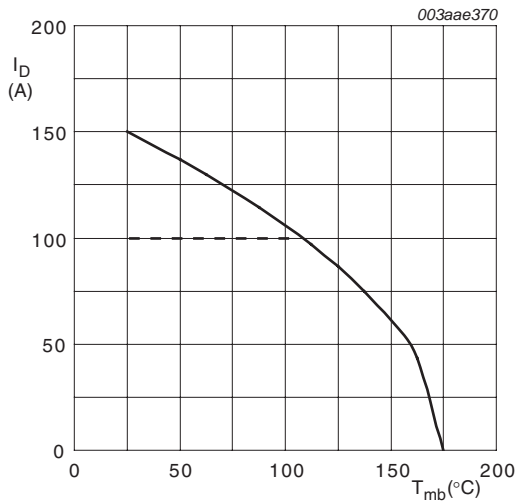
[2] Accumulated pulse duration not to exceed 5mins.

[3] Continuous current is limited by package.

[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

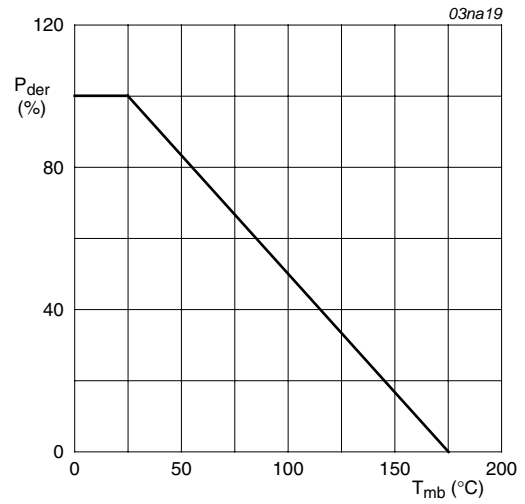
[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.



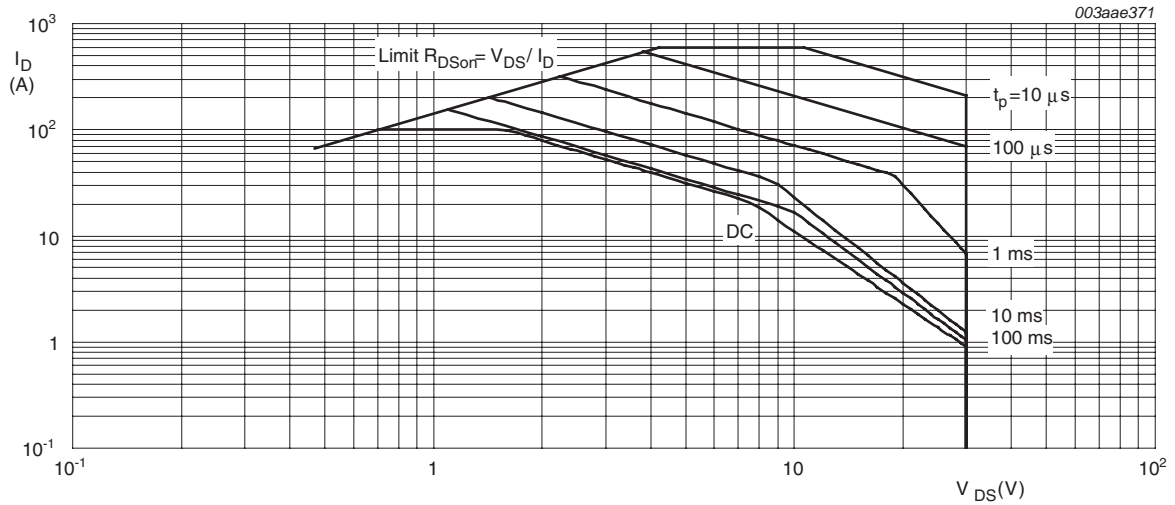
$V_{GS} \geq 10V$   
 (1) Capped at 100 A due to package.

**Fig 1. Continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



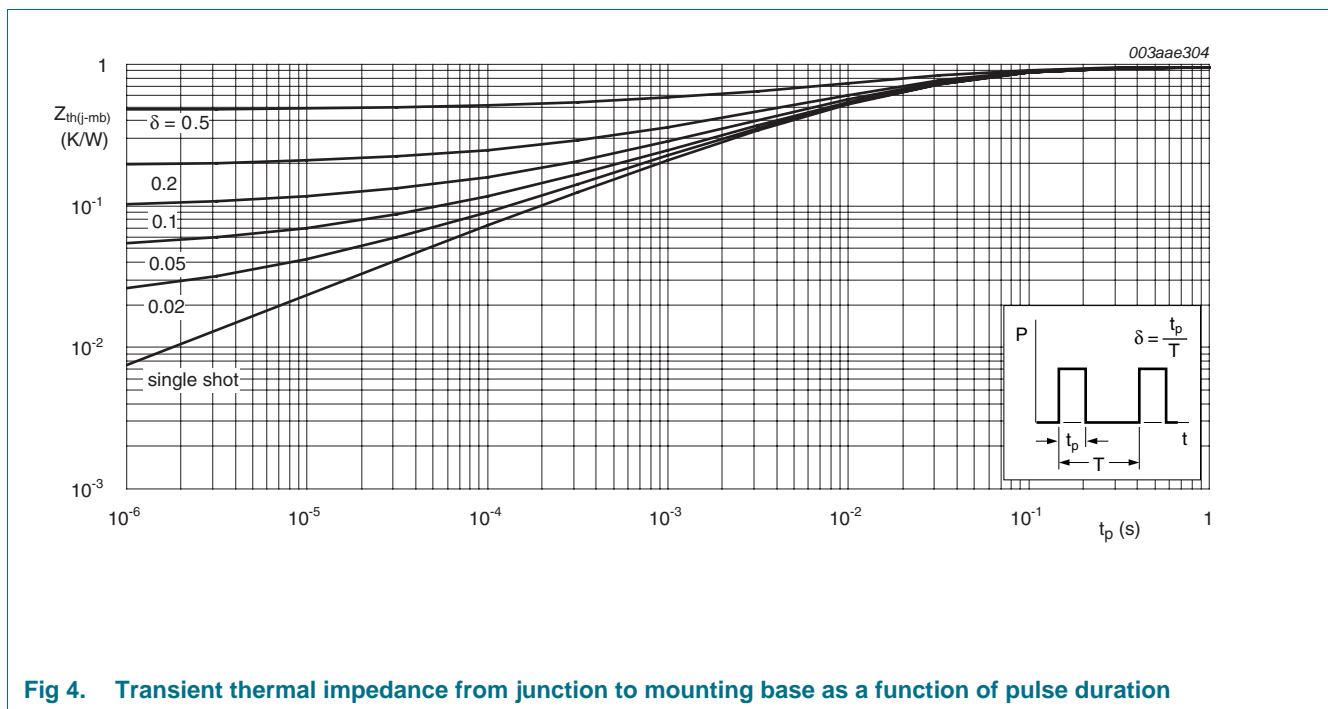
$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

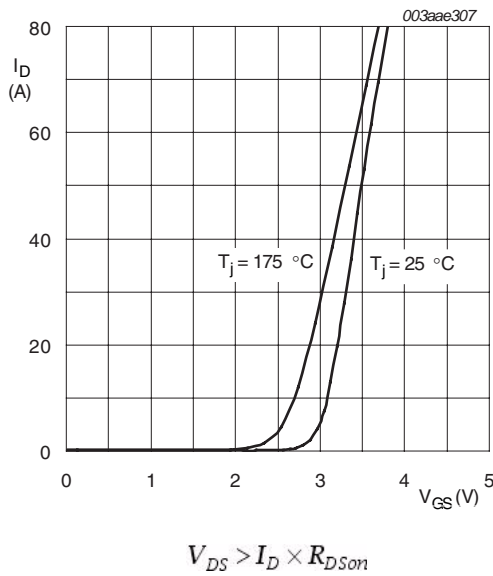
## 6. Characteristics

Table 6. Characteristics

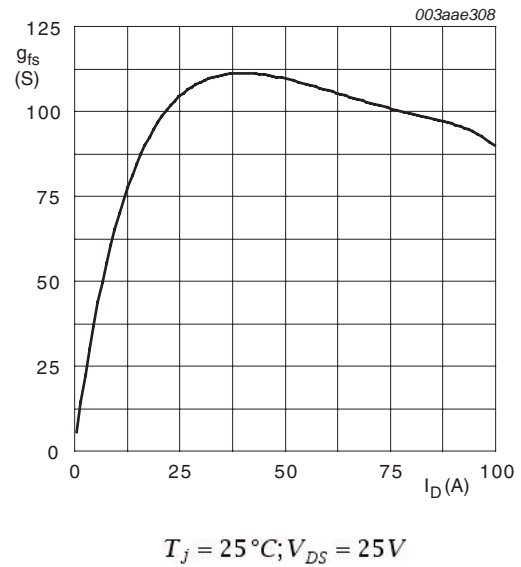
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 9</a> ; see <a href="#">Figure 10</a>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 9</a>	-	-	3.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 9</a>	0.8	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	$\mu A$
		$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.02	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	-	3.3	3.9	m $\Omega$
		$V_{GS} = 5 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	-	4.6	5.8	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	-	5.3	7.2	m $\Omega$
		$V_{GS} = 10 V; I_D = 25 A; T_j = 175 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 11</a>	-	-	7.4	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V$ ; see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	78	-	nC
		$I_D = 25 A; V_{DS} = 24 V; V_{GS} = 5 V$ ; see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	45	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V$ ; see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	15	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V$ ; see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	20	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 15</a>	-	3530	4707	pF
$C_{oss}$	output capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 14</a>	-	623	748	pF
$C_{riss}$	reverse transfer capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	-	381	522	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 25 V; R_L = 1 \text{ } \Omega; V_{GS} = 10 V$ ;	-	19	-	ns
$t_r$	rise time	$R_{G(ext)} = 10 \text{ } \Omega$	-	54	-	ns
$t_{d(off)}$	turn-off delay time		-	135	-	ns
$t_f$	fall time		-	83	-	ns
$L_D$	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ }^\circ C$	-	4.5	-	nH
$L_S$	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ }^\circ C$	-	7.5	-	nH

**Table 6. Characteristics ...continued**

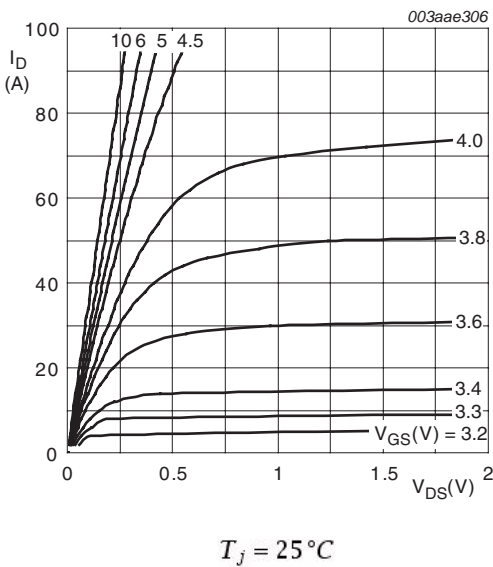
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 16</a>	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;	-	46	-	ns
$Q_r$	recovered charge	$V_{DS} = 25\text{ V}$	-	57	-	nC



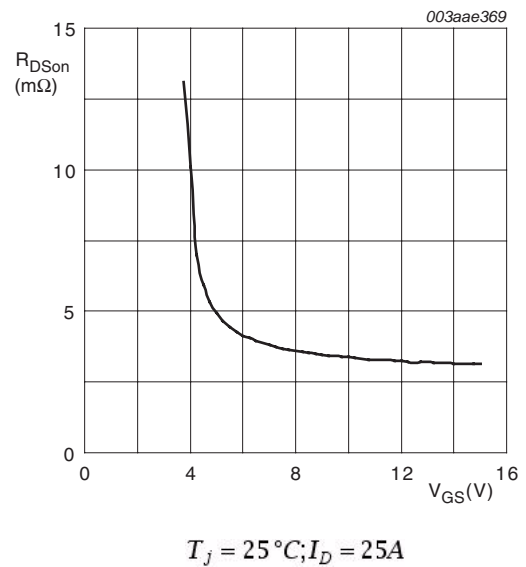
**Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



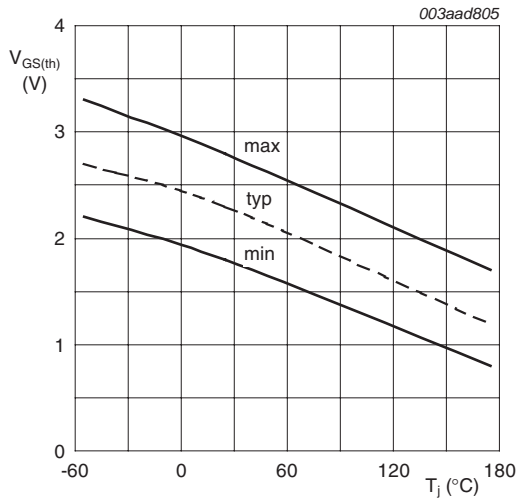
**Fig 6. Forward transconductance as a function of drain current; typical values**



**Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values**

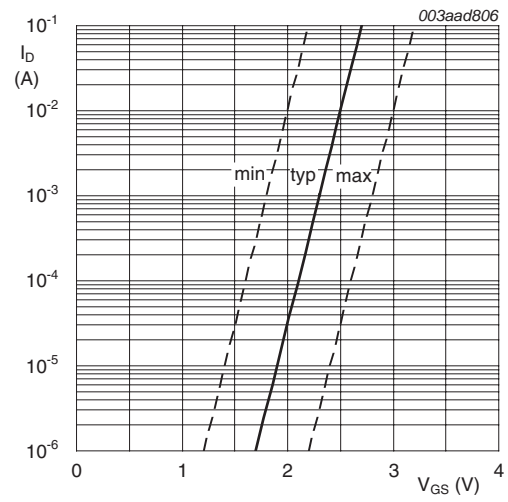


**Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values.**



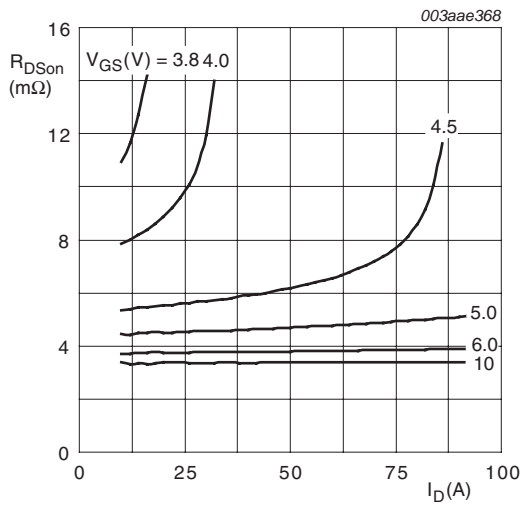
$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

**Fig 9. Gate-source threshold voltage as a function of junction temperature**



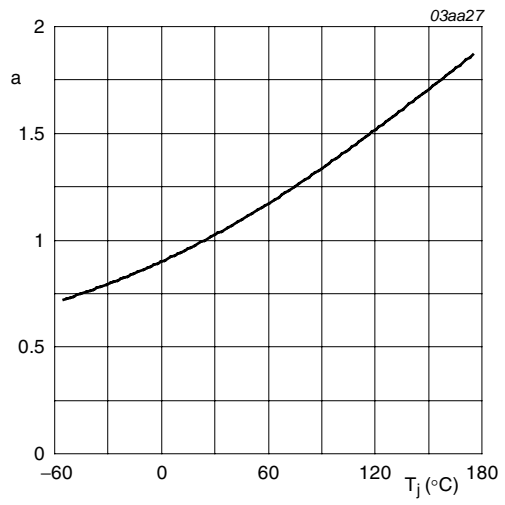
$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

**Fig 10. Sub-threshold drain current as a function of gate-source voltage**



$$T_j = 25^\circ\text{C}$$

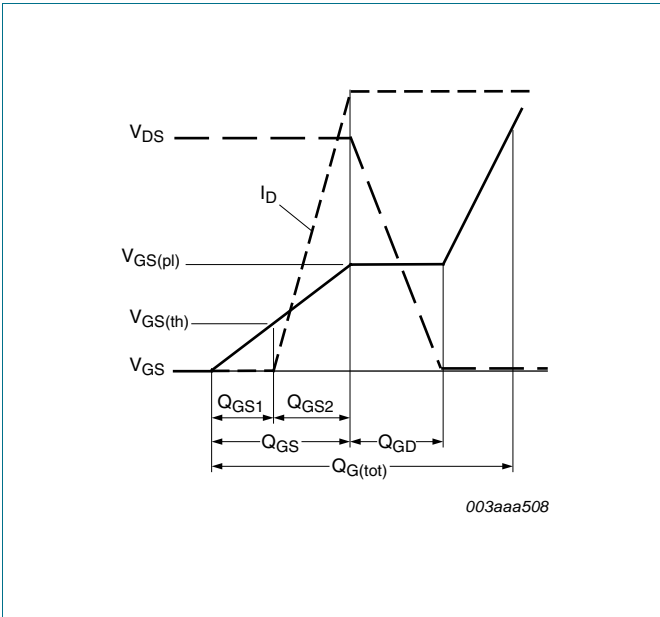
**Fig 11. Drain-source on-state resistance as a function of drain current; typical values**



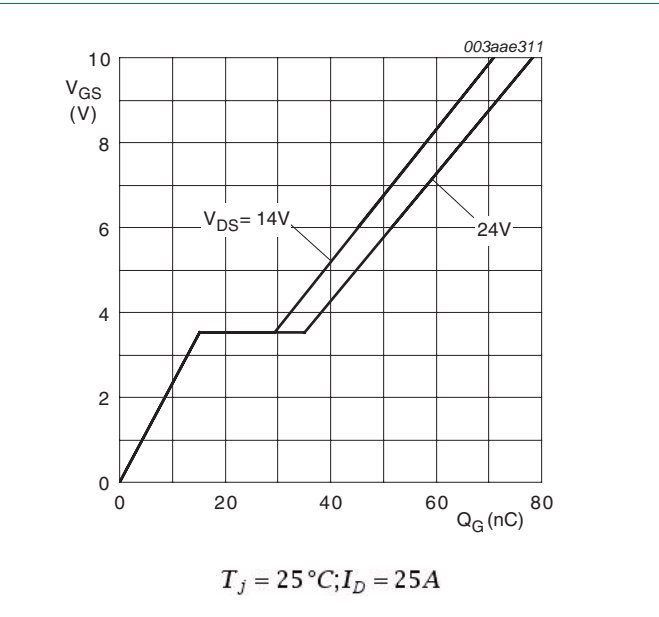
$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$

**Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature**

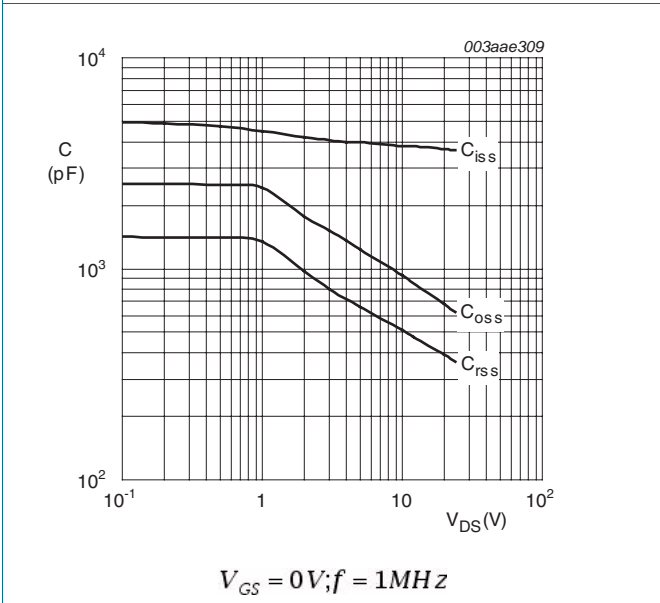




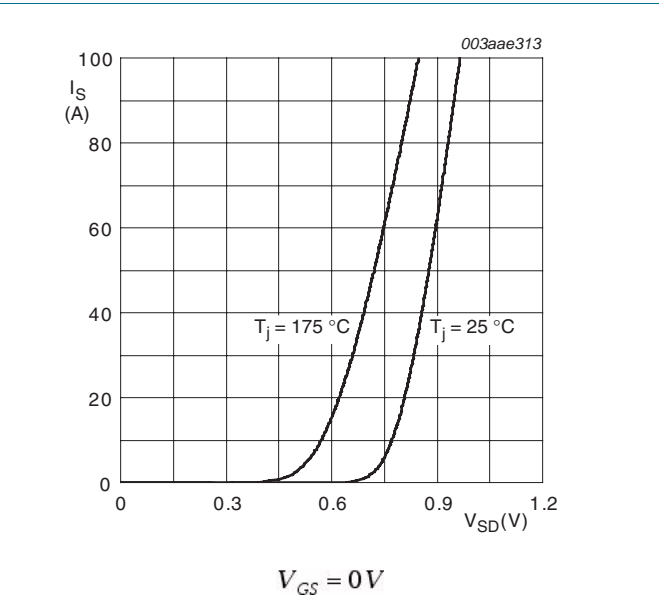
**Fig 13. Gate charge waveform definitions**



**Fig 14. Gate-source voltage as a function of gate charge; typical values**



**Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



**Fig 16. Source current as a function of source-drain voltage; typical values**

**7. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A

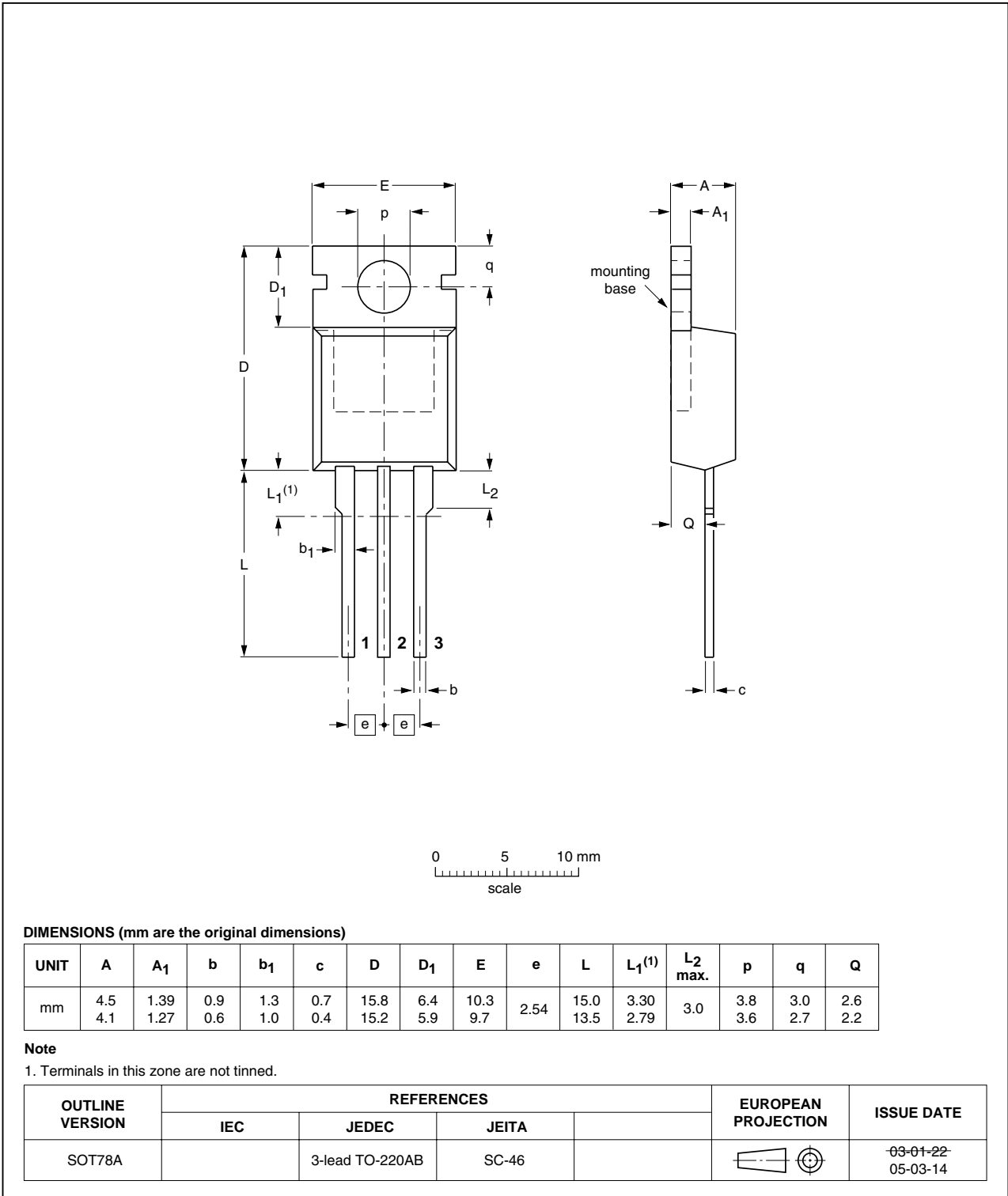


Fig 17. Package outline SOT78A (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK653R7-30C v.3	20101013	Product data sheet	-	BUK653R7-30C v.2
Modifications:	• Status changed from objective to product.			
BUK653R7-30C v.2	20100705	Objective data sheet	-	BUK653R7-30C v.1

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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